

Silicon NPN Power Transistors

2SC1235

DESCRIPTION

- With TO-66 package
- High collector-emitter voltage
: $V_{CEO}=300V$

APPLICATIONS

- For use in line-operated color TV chroma output circuits and sound output circuits.

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

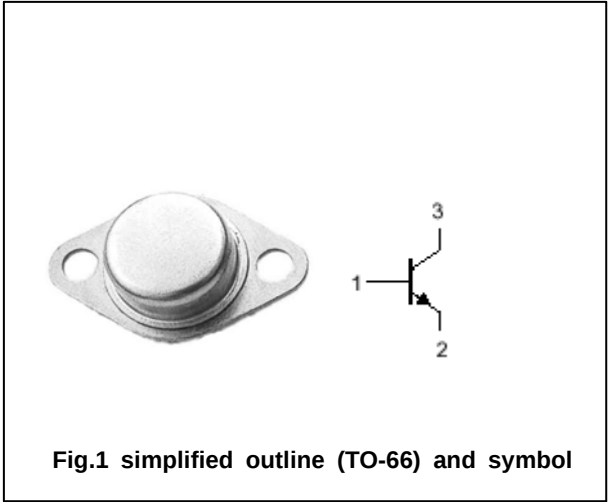


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings ($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		0.1	A
P_T	Collector power dissipation	$T_C=70^{\circ}C$	6.5	W
T_j	Junction temperature		150	$^{\circ}C$
T_{stg}	Storage temperature		-55~150	$^{\circ}C$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =50 μ A ; I _E =0	300			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =1mA ; I _B =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =50 μ A ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =50mA ; I _B =5mA			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =300V; I _E =0			5	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			5	μ A
h _{FE}	DC current gain	I _C =50mA ; V _{CE} =10V	30		160	
f _T	Transition frequency	I _C =10mA ; V _{CE} =20V		60		MHz

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PACKAGE OUTLINE

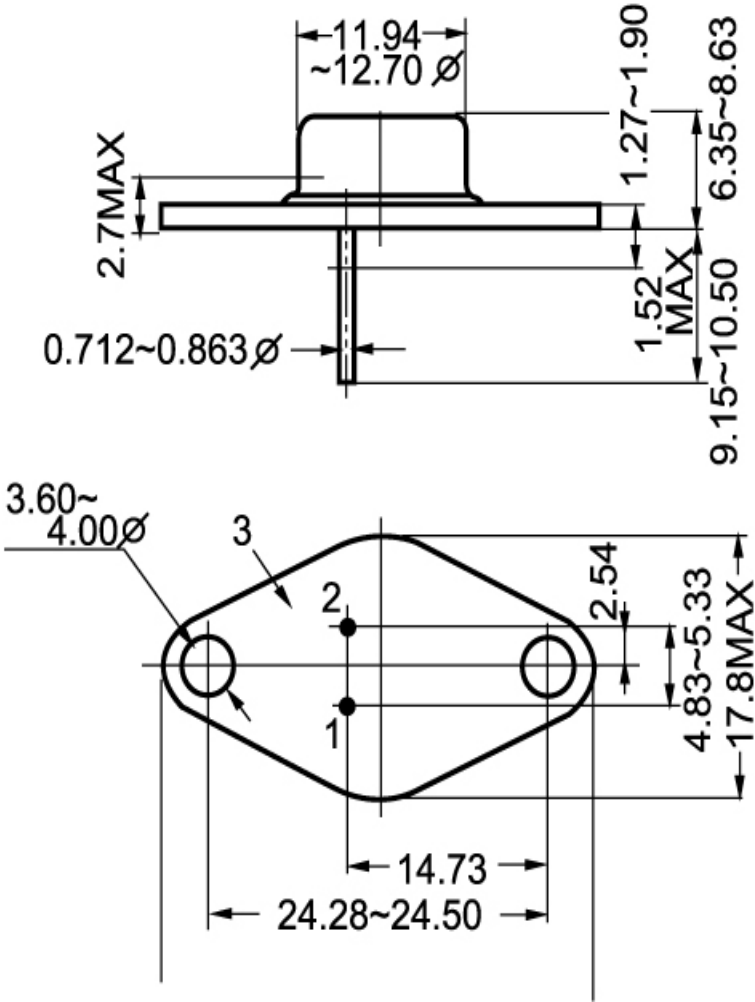


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)